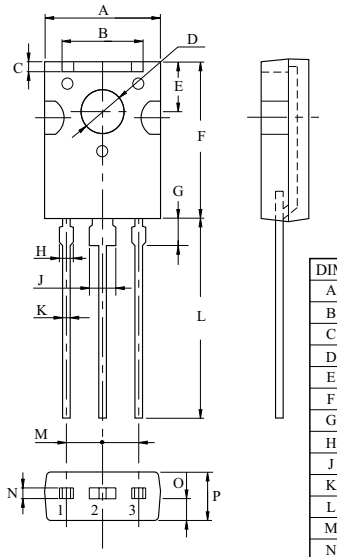
GENERAL PURPOSE DARLINGTON TRANSISTOR.

FEATURES

· High DC Current Gain : h_{FE}=3000(Min.)
(V_{CE}=2V, I_C=1A)



DIM	MILLIMETERS
A	8.3 MAX
B	5.8
C	0.7
D	Φ3.2±0.1
E	3.5
F	11.0±0.3
G	2.9 MAX
H	1.0 MAX
J	1.9 MAX
K	0.75±0.15
L	15.50±0.5
M	2.3±0.1
N	0.65±0.15
O	1.6
P	3.4 MAX

TO-126

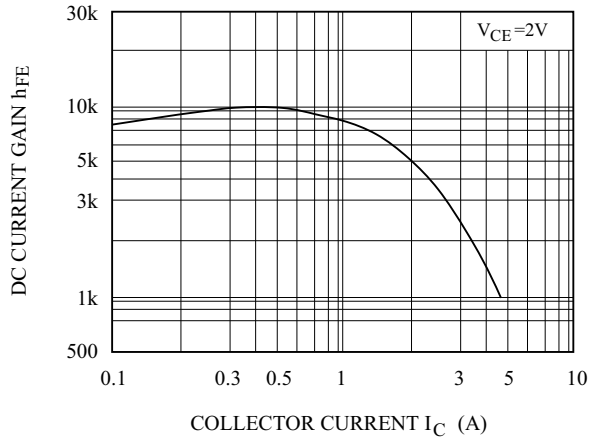
MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	4	A
Base Current	I_B	0.5	A
Collector Power Dissipation (Tc=25℃)	P_C	15	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃

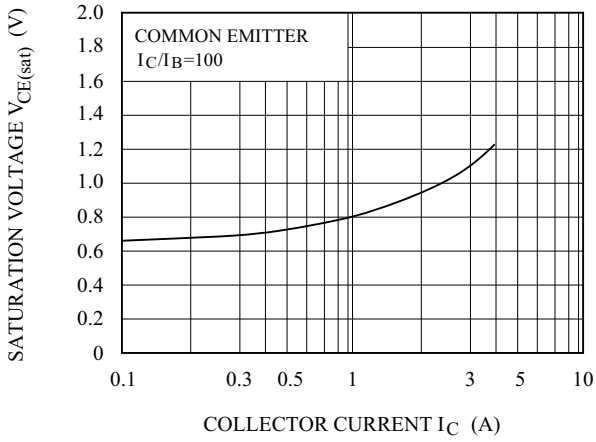
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=80V, I_E=0	-	-	20	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=10V, I_C=0	-	-	100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=10mA, I_B=0	60	-	-	V
DC Current Gain		h_{FE}(1)	V_{CE}=2V, I_C=1A	3000	-	-	
		h_{FE}(2)	V_{CE}=2V, I_C=3A	1000	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	I_C=3A, I_B=30mA	-	-	1.5	V
	Base-Emitter	$V_{BE(sat)}$	I_C=3A, I_B=30mA	-	-	2.0	

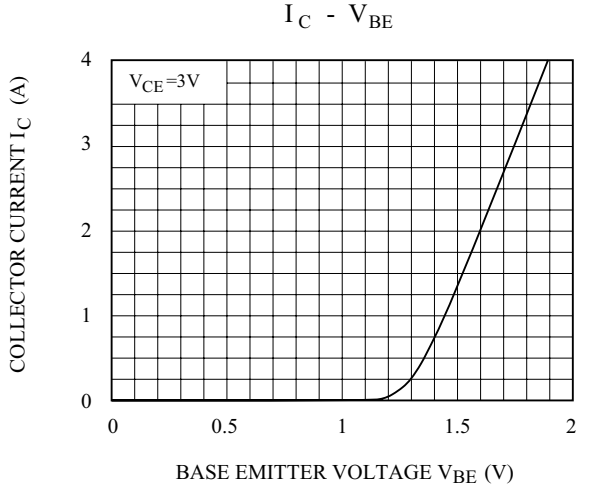
h_{FE} - I_C



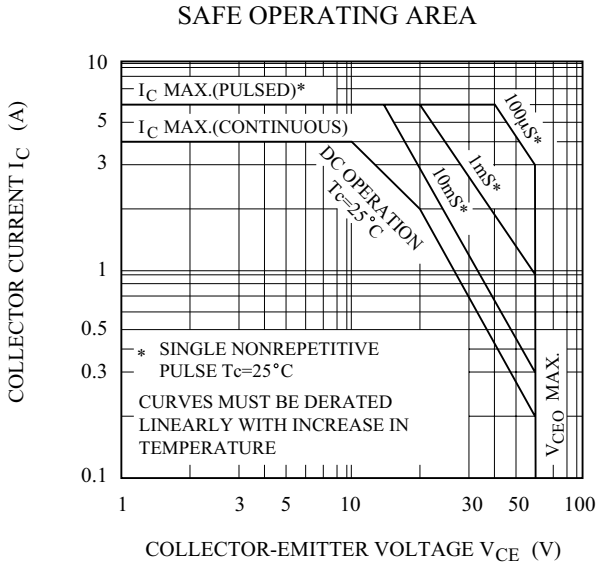
$V_{CE(sat)}$ - I_C



I_C - V_{BE}



SAFE OPERATING AREA



P_C - Ta